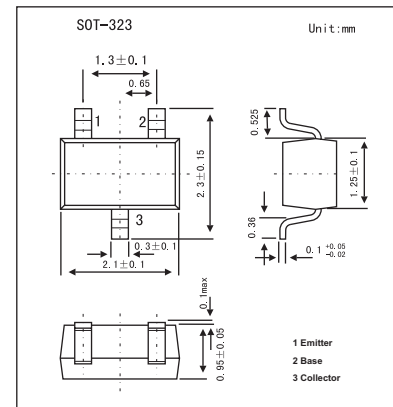
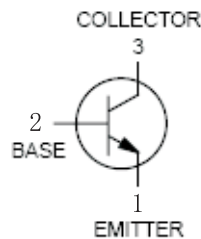


## General Purpose Transistor

## MMBT2907AW

## ■ Features

- General purpose transistor.
- Pb-Free package is available.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector-emitter voltage	$V_{CEO}$	-60	V
Collector-base voltage	$V_{CBO}$	-60	V
Emitter-base voltage	$V_{EBO}$	-5	V
Collector current	$I_C$	-600	mA
Total Device Dissipation FR-5 Board	$P_D$	150	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Junction temperature	$T_J$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

\* FR-5 = 1.0X 0.75 X0.062 in.

## MMBT2907AW

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -10 mA, I <sub>B</sub> = 0	-60			V
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = -10 mA, I <sub>E</sub> = 0	-60			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -10 μA, I <sub>C</sub> = 0	-5			V
Base cutoff current	I <sub>BL</sub>	V <sub>CE</sub> = -30 V, V <sub>EB(off)</sub> = -0.5 V			-50	nA
Collector cutoff current	I <sub>CEX</sub>	V <sub>CE</sub> = -30 V, V <sub>EB(off)</sub> = -0.5 V			-50	nA
DC current gain *	H <sub>FE</sub>	I <sub>C</sub> = -0.1 mA, V <sub>CE</sub> = -10 V	75			
		I <sub>C</sub> = -1.0 mA, V <sub>CE</sub> = -10 V	100			
		I <sub>C</sub> = -10 mA, V <sub>CE</sub> = -10 V	100			
		I <sub>C</sub> = -150 mA, V <sub>CE</sub> = -10 V	100			
		I <sub>C</sub> = -500 mA, V <sub>CE</sub> = -10 V	50			
Collector-emitter saturation voltage *	V <sub>CE(sat)</sub>	I <sub>C</sub> = -150 mA, I <sub>B</sub> = -15 mA			-0.4	V
		I <sub>C</sub> = -500 mA, I <sub>B</sub> = -50 mA			-1.6	
Base-emitter saturation voltage *	V <sub>BE(sat)</sub>	I <sub>C</sub> = -150 mA, I <sub>B</sub> = -15 mA			-1.3	
		I <sub>C</sub> = -500 mA, I <sub>B</sub> = -50 mA			-2.6	
Current-gain-bandwidth product	f <sub>r</sub>	I <sub>C</sub> = -50 mA, V <sub>CE</sub> = 20 V, f = 100 MHz	200			MHz
Output capacitance	C <sub>obo</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1.0 MHz			8.0	pF
Input capacitance	C <sub>ibo</sub>	V <sub>EB</sub> = -2.0 V, I <sub>C</sub> = 0, f = 1.0 MHz			30	pF
Turn?on time	t <sub>on</sub>	V <sub>CC</sub> = -30 V, I <sub>C</sub> = -150 mA, I <sub>B1</sub> = -15 mA			45	ns
Delay time	t <sub>d</sub>				10	ns
Rise time	t <sub>r</sub>				40	ns
Storage time	t <sub>s</sub>				80	ns
Fall time	t <sub>f</sub>				30	ns
Turn?off time	t <sub>off</sub>	V <sub>CC</sub> = -6.0 V, I <sub>C</sub> = -150 mA, I <sub>B1</sub> = I <sub>B2</sub> = 15 mA			100	ns

\* Pulse test: pulse width ≤ 300 μs, duty cycle ≤ 2.0%.

## ■ Marking

Marking	20
---------	----